(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property Organization
International Bureau

(43) International Publication Date
26 August 2004 (26.08.2004)

PCT

(10) International Publication Number
WO 2004/073047 A3

(51) International Patent Classification[7]: H01L 29/792, 21/336

(21) International Application Number: PCT/US2004/000492

(22) International Filing Date: 8 January 2004 (08.01.2004)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
10/358,589 5 February 2003 (05.02.2003) US

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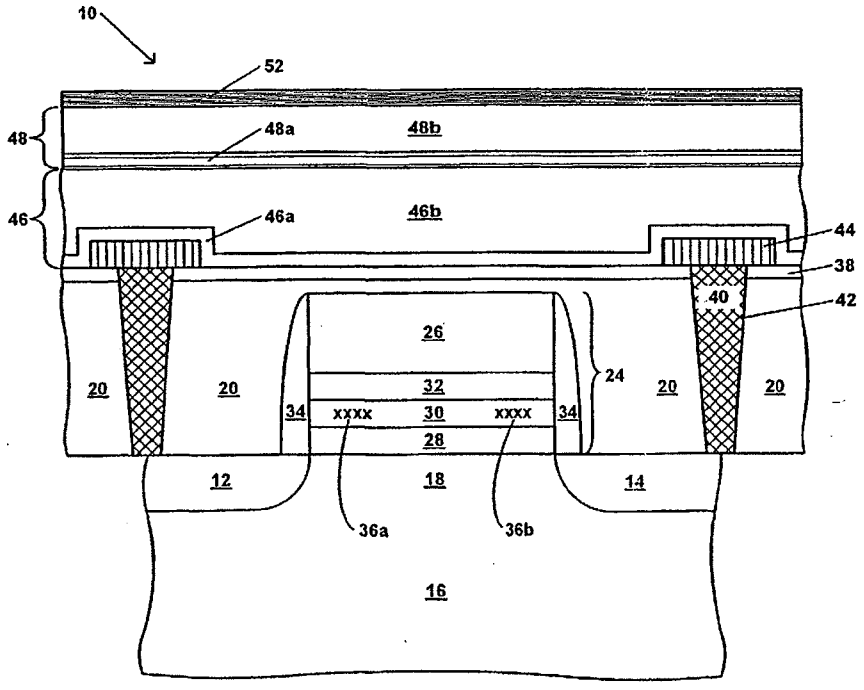
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(81) Designated States *(unless otherwise indicated, for every kind of national protection available)*: AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA, CH, CN,

[Continued on next page]

(54) Title: UV-BLOCKING LAYER FOR REDUCING UV-INDUCED CHARGING OF SONOS DUAL-BIT FLASH MEMORY DEVICES IN BEOL PROCESSING



(57) Abstract: A method of protecting a SONOS flash memory cell (24) from UV-induced charging, including fabricating a SONOS flash memory cell (24) in a semiconductor device (10, 50); and depositing over the SONOS flash memory cell (24) at least one UV-protective layer (38, 46, 48 or 52), the UV-protective layer including a substantially UV-opaque material. A SONOS flash memory device (10, 50), including a SONOS flash memory cell (24); and at least one UV-protective layer (38, 46, 48 or 52), in which the UV-protective layer comprises a substantially UV-opaque material, is provided.

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CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NA, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, YU, ZA, ZM, ZW.

(84) **Designated States** *(unless otherwise indicated, for every kind of regional protection available)*: ARIPO (BW, GH, GM, KE, LS, MW, MZ, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IT, LU, MC, NL, PT, RO, SE, SI, SK, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

Published:

— *with international search report*

— *before the expiration of the time limit for amending the claims and to be republished in the event of receipt of amendments*

(88) **Date of publication of the international search report:**
7 October 2004

For two-letter codes and other abbreviations, refer to the "Guidance Notes on Codes and Abbreviations" appearing at the beginning of each regular issue of the PCT Gazette.